



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

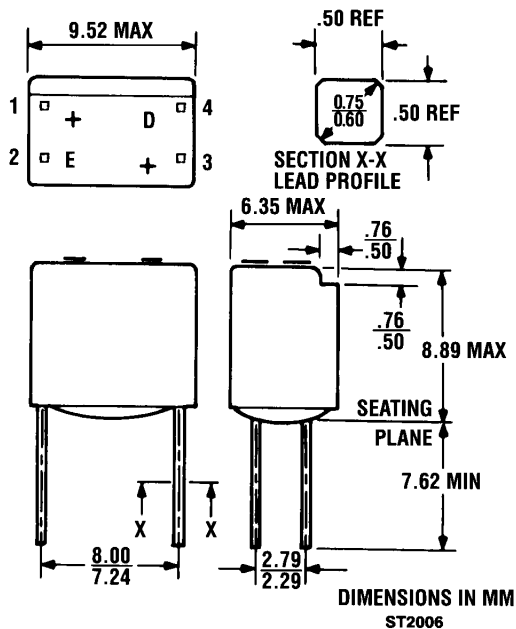
Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



PACKAGE DIMENSIONS



DESCRIPTION

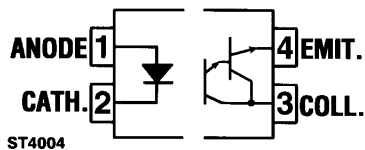
The H24A series consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor. The devices are housed in a low-cost plastic package with lead spacing compatible with a dual in-line package.

FEATURES

- 4-pin configuration
- Small package size and low cost
- UL recognized-file E51868

APPLICATIONS

- Digital logic inputs
- Microprocessor inputs
- Industrial controls



Equivalent Circuit

ABSOLUTE MAXIMUM RATINGS

TOTAL PACKAGE

Storage temperature -55°C to 85°C
Operating temperature -55°C to 85°C
Lead solder temperature 260°C for 5 sec

INPUT DIODE

Power dissipation (25°C ambient) 100 mW
Derate linearly (above 25°C) 1.67 mW/°C
Continuous forward current 60 mA
Reverse voltage 4 V

DETECTOR

Power dissipation (25°C ambient) 150 mW
Derate linearly (above 25°C) 2.5 mW/°C
V_{CEO} 30 V
V_{ECO} 6 V
Continuous forward current 100 mA

ELECTRICAL CHARACTERISTICS (25°C Temperature Unless Otherwise Specified)

INDIVIDUAL COMPONENT CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
INPUT DIODE						
Forward voltage	V_F			1.7	V	$I_F=60\text{ mA}$
Reverse current	I_R			1	μA	$V_R=3\text{ V}$
Reverse breakdown voltage	$V_{BR(R)}$	4			V	$I_R=10\ \mu\text{A}$
Capacitance	C_i		30		pF	$V=0, f=1\text{ MHz}$
OUTPUT DETECTOR						
Breakdown voltage Collector to emitter	BV_{CEO}	30			V	$I_C=1\text{ mA}, I_F=0$
Breakdown voltage Emitter to Collector	BV_{ECO}	7			V	$I_C=100\ \mu\text{A}, I_F=0$
Collector dark current	I_{CEO}		5	100	nA	$V_{CE}=10\text{ V}, I_F=0$
Capacitance	C_{CE}		3.3		pF	$V_{CE}=5\text{ V}, f=1\text{ MHz}$

TRANSFER CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
DC CURRENT TRANSFER RATIO						
H24A1	I_C	10.0			mA	$I_F=10\text{ mA}, V_{CE}=10\text{ V}$
H24A2	I_C	2.0			mA	$I_F=10\text{ mA}, V_{CE}=10\text{ V}$
Saturation voltage	$V_{CE(SAT)}$		0.1	0.4	V	$I_F=10\text{ mA}, I_C=0.5\text{ mA}$
Turn-on time	t_{on}		9		μs	$I_C=2\text{ mA}, V_{CE}=10\text{ V}, R_L=100\ \Omega$
Turn-off time	t_{off}		4		μs	$I_F=2\text{ mA}, V_{CE}=10\text{ V}, R_L=100\ \Omega$
Turn-on time	t_{on}		6.5		μs	$I_F=10\text{ mA}, V_{CE}=5\text{ V}, R_L=10\text{K}\Omega$
Turn-off time	t_{off}		165		μs	$I_F=10\text{ mA}, V_{CE}=5\text{ V}, R_L=10\text{K}\Omega$

ISOLATION CHARACTERISTICS

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
Surge isolation voltage	V_{ISO}	6000			V_{Peak}	1 Minute
Steady-state isolation voltage	V_{ISO}	5300			V_{RMS}	1 Minute
Isolation resistance	R_{ISO}	10^{11}			ohms	$V_{i,o}=500\text{ VDC}$
Isolation capacitance	C_{ISO}		0.5		pF	$V_{i,o}=0, f=1\text{ MHz}$

TYPICAL ELECTRICAL CHARACTERISTIC CURVES
(25°C Free Air Temperature Unless Otherwise Specified)

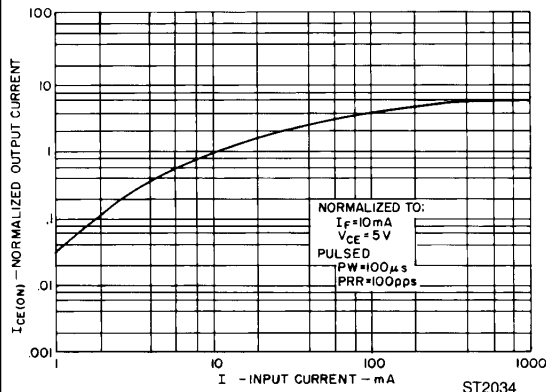


Fig. 1. Output Current vs. Input Current

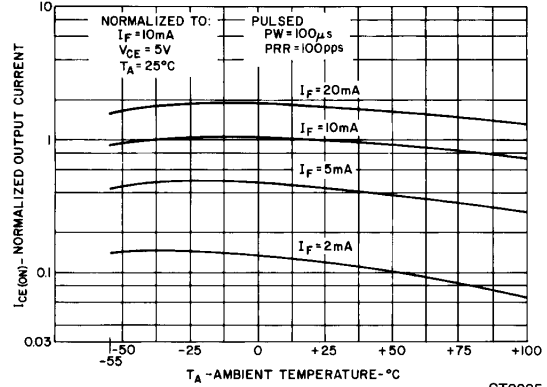


Fig. 2. Output Current vs. Temperature

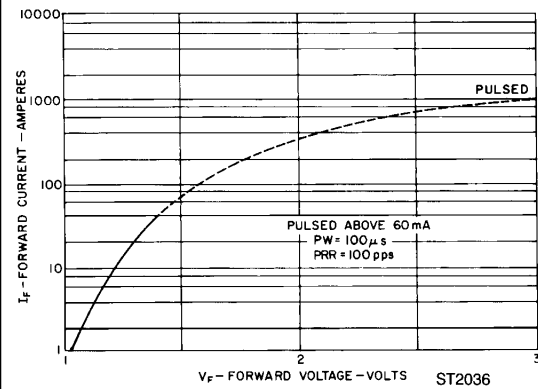


Fig. 3. Input Characteristics

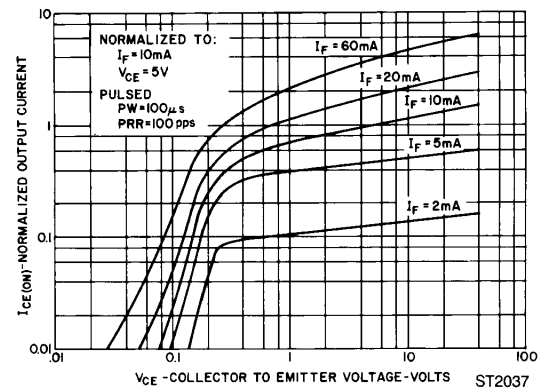


Fig. 4. Output Characteristics

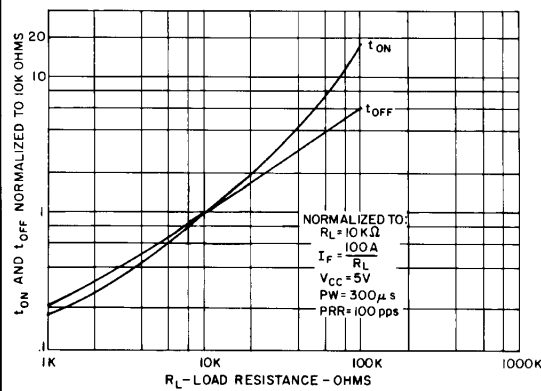


Fig. 5. Switching Speed vs. R_L

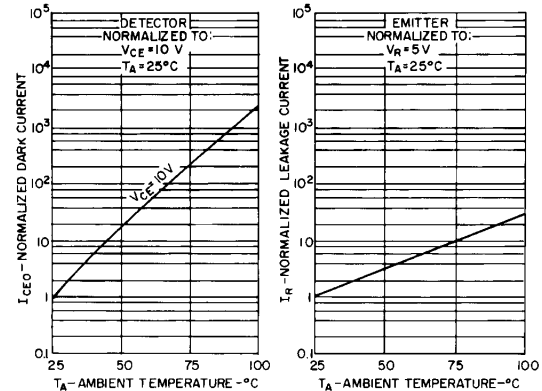


Fig. 6. Leakage Current vs. Temperature



PHOTOTRANSISTOR OPTOCOUPERS

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